

3875081 G E SOLID STATE

01E 17718

DT-25-13

Silicon Controlled Rectifiers

S2600B, S2600D, S2600M, S2600N

File Number 1693

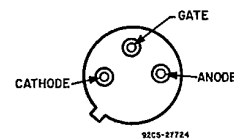
High Voltage, Medium Current Silicon Controlled Rectifiers

For Power Switching, Power Control and Ignition Applications

Features:

- 800V, 125 Deg. C T_J Operating
- High dv/dt and di/dt Capability
- Low Switching Losses
- High Pulse Current Capability
- Low Forward and Reverse Leakage
- Sipos Oxide Glass Multilayer Passivation System
- Advanced Unisurface Construction
- Precise Ion Implanted Diffusion Source

TERMINAL DESIGNATIONS



Low-Profile TO-205

The S2600 series are high voltage, medium current silicon controlled rectifiers designed for switching AC and DC currents. The types within the series differ in their voltage ratings: the voltage ratings are identified by suffix letters in the type designations.

All types utilize the low-profile TO-205 package.

These Thyristors feature an advanced unisurface construction with a multilayer glass passivation system for improved reliability performance at high junction operating temperatures. Their dv/dt , di/dt capability and low switching losses make them suitable for applications such as lighting, power-switching, motor speed control and crowbars.

MAXIMUM RATINGS, Absolute-Maximum Values:

	S2600B	S2600D	S2600M	S2600N	
VDRM	200	400	600	800	V
VRRM	200	400	600	800	V
IT (RMS) ($T_C = 65^\circ\text{C}$)			7		A
IT (av) ($T_C = 65^\circ\text{C}$, $\theta = 180^\circ$)			4.5		A
ITSM (for 1 full cycle)			100		A
di/dt			200		A/ μs
I^2T (at 8.3 ms)			40		A ^2s
(at 1.5 ms)			30		A ^2s
PGM (for 10 μs max.)			15		W
PG (av) (Averaging time 10ms max.)			0.5		W
T Storage			-65 to 150		$^\circ\text{C}$
T_J			-65 to 125		$^\circ\text{C}$

3875081 G E SOLID STATE

01E 17719 D T-25-13
Silicon Controlled Rectifiers**S2600B, S2600D, S2600M, S2600N**ELECTRICAL CHARACTERISTICS, at Case Temperature (T_c) = 25°C Unless Otherwise Specified

CHARACTERISTIC	SYMBOL	LIMITS			UNITS
		S2600 FAMILY			
		MIN.	TYP.	MAX.	
Repetitive Peak Forward and Reverse Blocking Current Rated VDRM and VRRM, Gate Open at TC = 125° C	IDROM IRROM	— —	— —	50 2	μA mA
Forward "On State" Voltage ITM = 30A	VTM	—	1.8	2.6	V
Gate Trigger Current (dc) VD = 12 Vdc RL = 30 Ohms	IGT	—	10	15	mA
Gate Trigger Voltage (dc) VD = 12 Vdc, RL = 30 Ohms VD = VDRM, RL = 500 Ohms, TC = 125° C	VGT	— 0.2	1 —	1.5 —	V
Holding Current VD = 12 Vdc, IT (initial) = 200mA	IH	—	15	—	mA
Critical Rate of Rise of Off-State Voltage (Exponential Waveform) TC = 125° C, Gate Open, VD = VDRM S2600B, S2600D S2600M S2600N	dv/dt	— — — —	— 150 125 75	— — — —	V/μS
Turn-On Time IT = 2A, VD = VDRM IG = 80mA	tgt	—	1.2	—	μS
Turn-Off Time VD = VDRM, TC = 75° C, dv/dt = 20V/μS IT = 2A for 50 μS, di/dt = 10A/μS IG = 80mA at Turn-On	tq	—	65	—	μS
Thermal Resistance Junction to Case Junction to Ambient	RθJC RθJA	— —	— —	7 150	°C/W

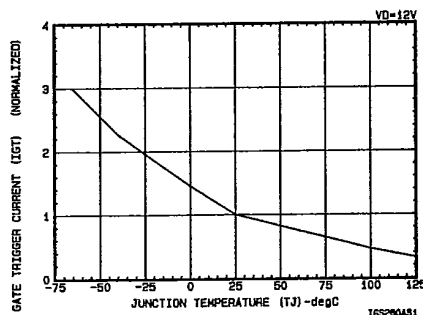


Fig. 1 - Typical Gate Trigger Current Vs. Temperature

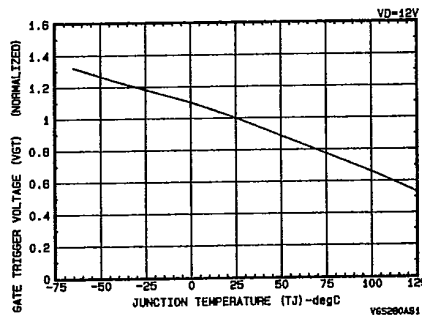


Fig. 2 - Typical Gate Trigger Voltage Vs. Temperature

3875081 G E SOLID STATE
Silicon Controlled Rectifiers

01E 17720 D T-25-13

S2600B, S2600D, S2600M, S2600N

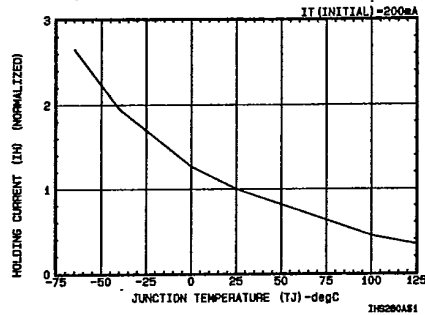


Fig. 3 - Typical Holding Current Vs. Temperature

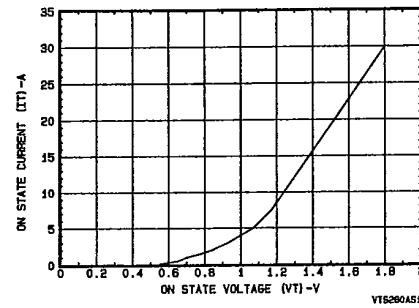


Fig. 4 - Typical On State Voltage Vs. Current

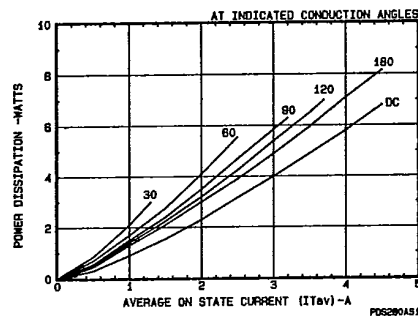


Fig. 5 - Maximum Power Dissipation Vs. Average Current

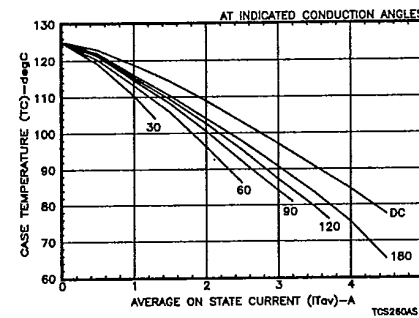


Fig. 6 - Maximum Case Temperature Vs. Average Current

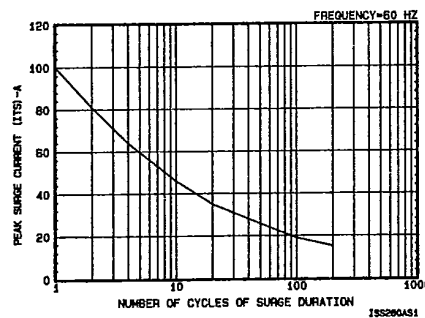


Fig. 7 - Peak Surge Current Vs. Duration